

Silicon PNP Power Transistors

2SB600

DESCRIPTION

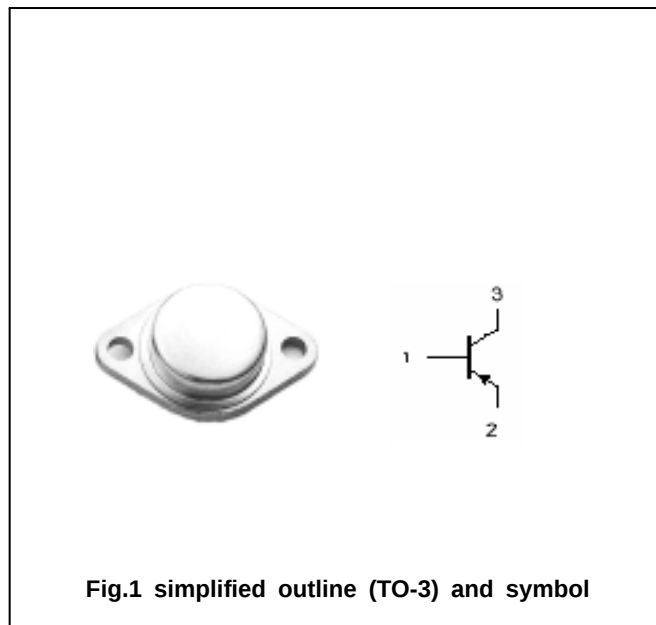
- With TO-3 package
- High power dissipations
- Complement to type 2SD555

APPLICATIONS

- For use in audio and power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	Open base	-200	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-10	A
P_C	Collector power dissipation	$T_C = 25$	200	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~200	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-25mA ; I _B =0	-200			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-10A; I _B =-1A			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-10A; I _B =-1A			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-200V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-2A ; V _{CE} =-5V	20			
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-10V	4			MHz

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PACKAGE OUTLINE

